

UNISONIC TECHNOLOGIES CO., LTD

4128D

Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

MIDDLING VOLTAGE **FAST-SWITCHING NPN** POWER TRANSISTOR

DESCRIPTION

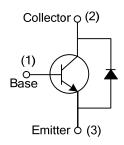
The UTC 4128D is a middling voltage NPN power transistor. it uses UTC's advanced technology to provide customers with high switching speed and high reliability, etc.

The UTC 4128D is suitable for commonly power amplifier circuit, electronic ballasts and energy-saving light etc.

FEATURES

- * High switching speed
- * High reliability

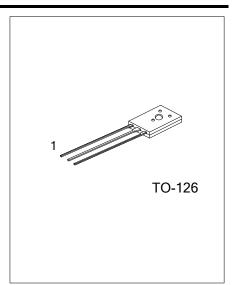
SYMBOL



ORDERING INFORMATION

Ordering Number		Dealtons	Pin Assignment			Dealine
Lead Free	Halogen Free	Package	1	2	3	Packing
4128DL-T60-K	4128DG-T60-K	TO-126	В	С	Е	Bulk
Note: Pin Assignment: B: B:	ter					

4128DL-T60-T - (1)Packing Type (1) B: Bulk (2)Package Type (2) T60: TO-126 - (3)Lead Free (3) L: Lead Free, G: Halogen Free



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage (V _{BE} =0)		V _{CES}	350	V
Collector-Emitter Voltage (I _B =0)		V_{CEO}	200	V
Emitter-Base Voltage		V_{EBO}	7	V
Collector Current	DC	Ic	5	Α
	Pulse (Note 2)	I _{CP}	10	Α
Base Current	DC	Ι _Β	2	Α
	Pulse (Note 2)	I _{BP}	4	Α
Total Dissipation		Pc	40	W
Junction Temperature		T_J	150	°C
Storage Temperature Range		T _{STG}	-55~+150	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θ_{JC}	3.125	°C/W

■ ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =1mA, I _B =0				V
Collector-Emitter Breakdown Voltage	BV_CEO	I _C =10mA, I _B =0	200			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=1$ mA, $I_C=0$	7			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =350V, I _E =0			100	μA
Collector-Emitter Cut-Off Current	I _{CEO}	V _{CE} =200V, I _B =0			50	μA
Emitter Cut-Off Current	I _{EBO}	V_{EB} =7V, I_C =0			10	μΑ
Outlier to a Facility of Outlier Walter	V _{CE(SAT)1}	I _C =1A, I _B =0.2A			0.8	V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)2}$	I _C =3A, I _B =0.6A			1.5	V
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	I _C =3A, I _B =0.6A			1.6	V
DO 0	h _{FE1}	I _C =0.8A,V _{CE} =5V	8		50	
DC Current Gain	h _{FE2}	$I_C=3A,V_{CE}=5V$	8			
Transition Frequency	f _T	I _C =0.5A, V _{CE} =10V	4			MHz
Storage Time	ts	V _{CC} =24V, I _C =0.5A, I _{B1} =-I _{B2} =0.1A			4	μs
Fall Time	t _F				0.7	μs

^{2.} Pulse Test: Pulse Width=5.0ms, Duty Cycle<10%.

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